



No.4918

2SJ362

P-Channel MOS Silicon FET  
Very High-Speed  
Switching Applications

**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

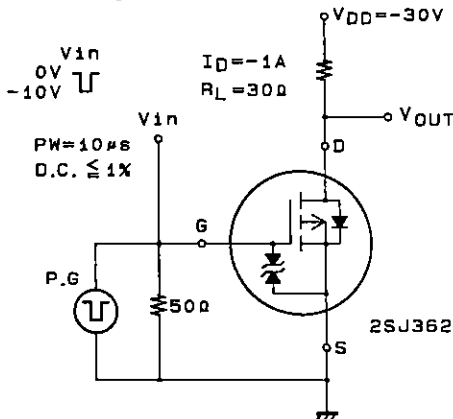
**Absolute Maximum Ratings at Ta = 25°C**

|                             |                  |                             |             | unit |
|-----------------------------|------------------|-----------------------------|-------------|------|
| Drain-to-Source Voltage     | V <sub>DSS</sub> |                             | -60         | V    |
| Gate-to-Source Voltage      | V <sub>GSS</sub> |                             | ±25         | V    |
| Drain Current (DC)          | I <sub>D</sub>   |                             | -2          | A    |
| Drain Current (Pulse)       | I <sub>DP</sub>  | PW ≤ 10 μs, duty cycle ≤ 1% | -8          | A    |
| Allowable Power Dissipation | P <sub>D</sub>   | Tc = 25°C                   | 20          | W    |
|                             |                  |                             | 1.0         | W    |
| Channel Temperature         | T <sub>ch</sub>  |                             | 150         | °C   |
| Storage Temperature         | T <sub>stg</sub> |                             | -55 to +150 | °C   |

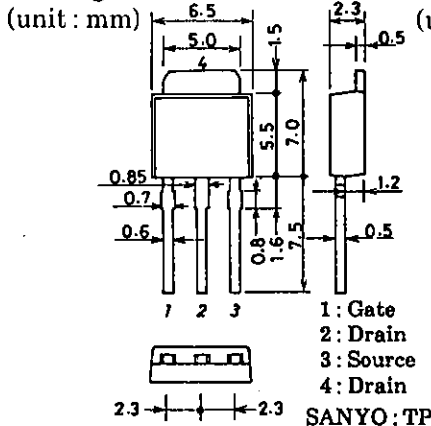
**Electrical Characteristics at Ta = 25°C**

|  |                      |   | min  | typ  | max  | unit |
|--|----------------------|---|------|------|------|------|
| D-S Breakdown Voltage                      | V <sub>(BR)DSS</sub> | I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0    | -60  |      |      | V    |
| G-S Breakdown Voltage                      | V <sub>(BR)GSS</sub> | I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0 | ±25  |      |      | V    |
| Zero-Gate Voltage Drain Current            | I <sub>DSS</sub>     | V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0   |      |      | -100 | μA   |
| Gate-to-Source Leakage Current             | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0   |      |      | ±10  | μA   |
| Gate-to-Source Cutoff Voltage              | V <sub>GS(off)</sub> | V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA | -1.5 |      | -2.5 | V    |
| Forward Transfer Admittance                | Y <sub>fs</sub>      | V <sub>DS</sub> = -10V, I <sub>D</sub> = -1A  | 1.2  | 2    |      | S    |
| Static Drain-to-Source ON-State Resistance | R <sub>DSON</sub>    | I <sub>D</sub> = -1A, V <sub>GS</sub> = -10V  |      | 300  | 400  | mΩ   |
|  | R <sub>DSON</sub>    | I <sub>D</sub> = -1A, V <sub>GS</sub> = -4V   |      | 450  | 650  | mΩ   |
| Input Capacitance                          | C <sub>iss</sub>     | V <sub>DS</sub> = -20V, f = 1MHz              |      | 240  |      | pF   |
| Output Capacitance                         | C <sub>oss</sub>     | V <sub>DS</sub> = -20V, f = 1MHz              |      | 150  |      | pF   |
| Reverse Transfer Capacitance               | C <sub>rss</sub>     | V <sub>DS</sub> = -20V, f = 1MHz              |      | 40   |      | pF   |
| Turn-ON Delay Time                         | t <sub>d(on)</sub>   | See specified Test Circuit.                   |      | 12   |      | ns   |
| Rise Time                                  | t <sub>r</sub>       |   |      | 16   |      | ns   |
| Turn-OFF Delay Time                        | t <sub>d(off)</sub>  |   |      | 85   |      | ns   |
| Fall Time                                  | t <sub>f</sub>       |   |      | 55   |      | ns   |
| Diode Forward Voltage                      | V <sub>SD</sub>      | I <sub>S</sub> = -2A, V <sub>GS</sub> = 0     | -1.0 | -1.5 |      | V    |

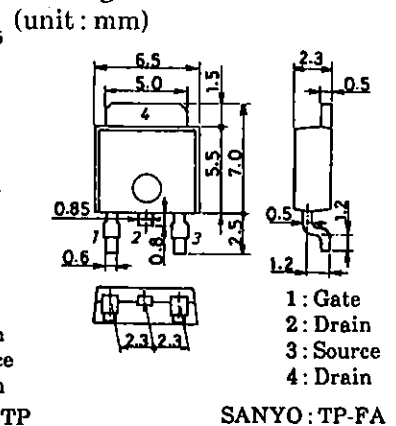
**Switching Time Test Circuit**

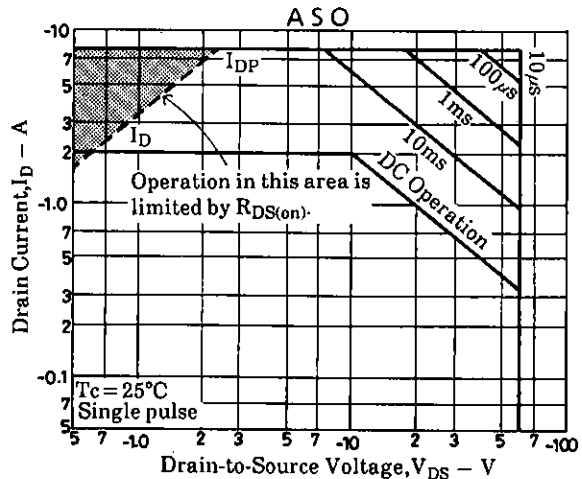
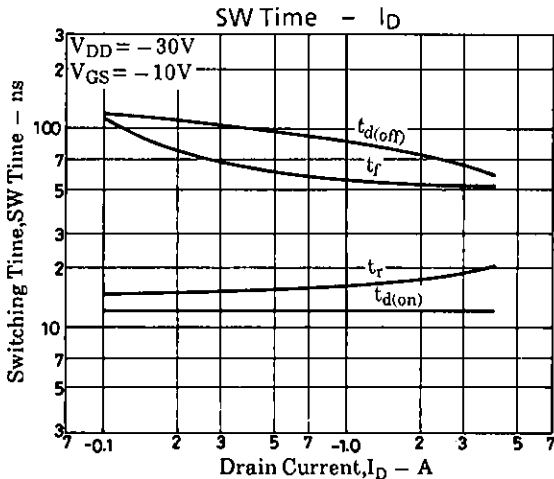
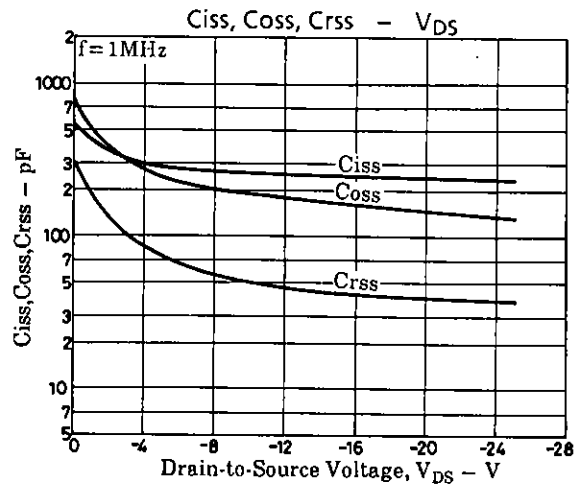
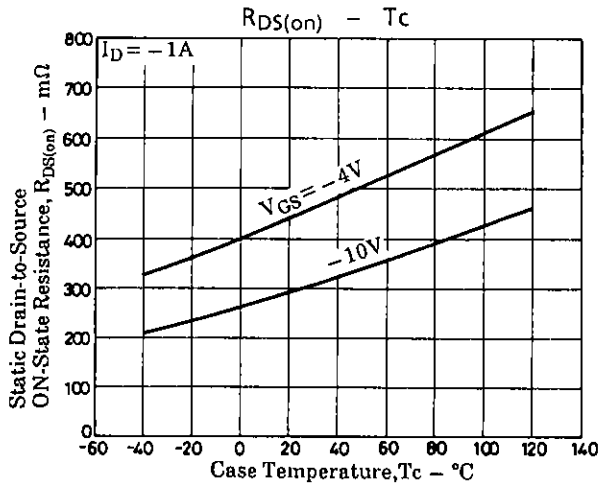
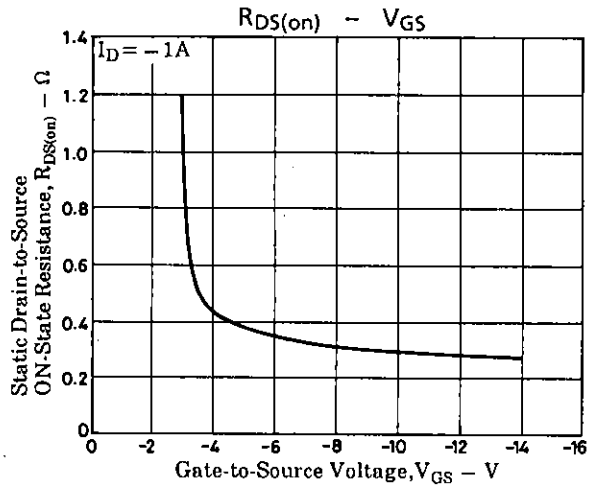
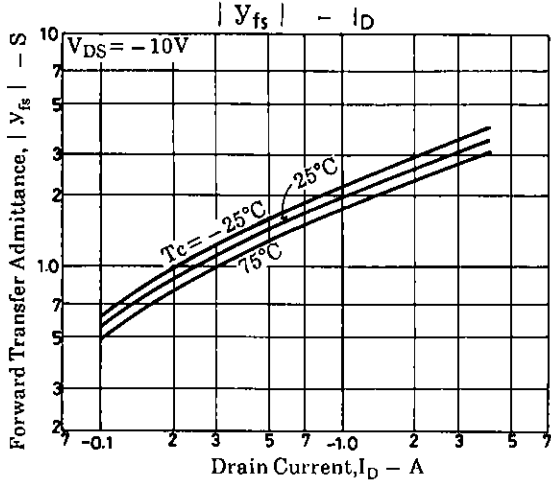
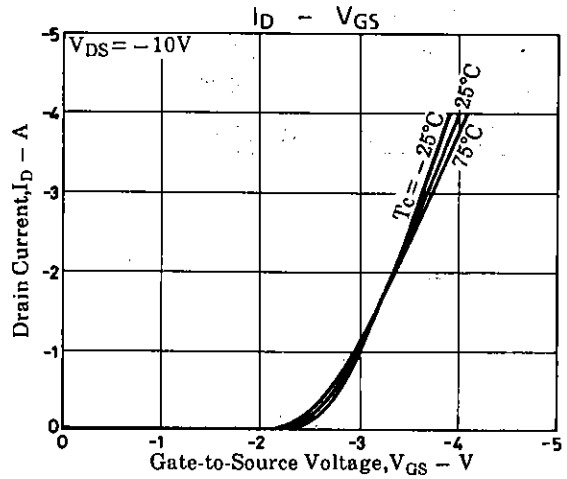
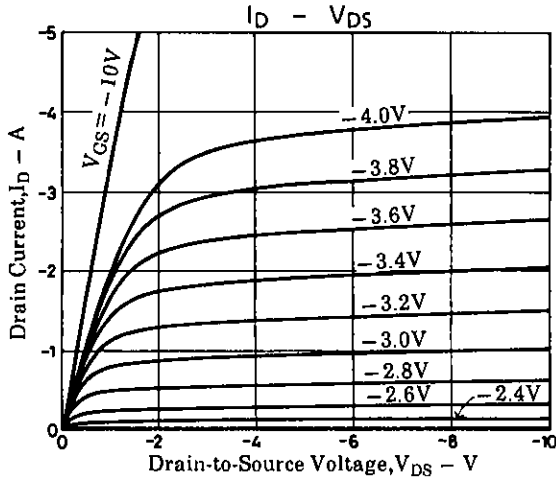


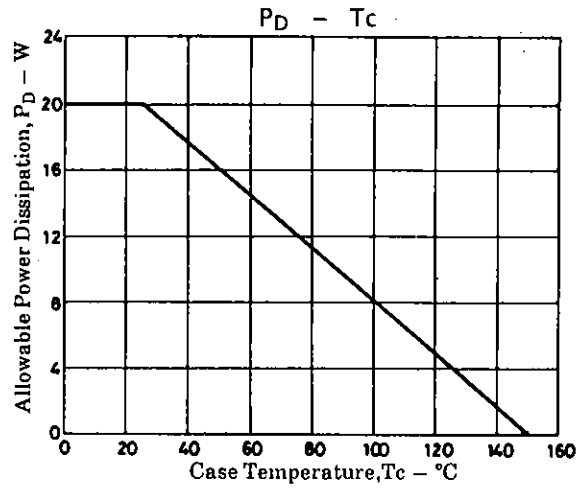
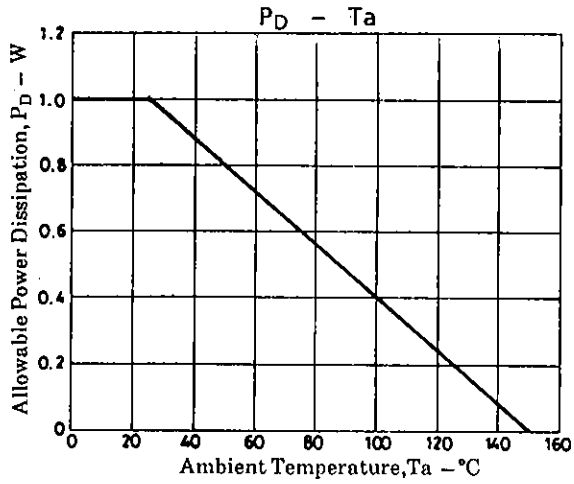
**Package Dimensions 2083B**



**Package Dimensions 2092B**







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